

Title (en)  
FABRICATION OF SUPPORTED POLYCRYSTALLINE ABRASIVE COMPACTS

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Application  
**EP 89119638 A 19891023**

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Abstract (en)  
[origin: EP0371251A2] Disclosed is a process for fabricating a supported polycrystalline diamond or CBN bi-layer compact which comprises forming a sintered polycrystalline or CBN compact which preferably is a thermally-stable compact. A cemented carbide support is separately formed. The compact and the support then are mated with a layer of diamond or CBN crystals having the largest dimension of between about 30 and 500 micrometers interposed therebetween. A source of catalyst/sintering aid material is provided in association with the layer of interposed crystals. The entire assembly then is subjected to HP/HT conditions and for a time adequate for converting the diamond or CBN crystals into a polycrystalline diamond or CBN layer and for producing the bi-layer supported compact of the present invention.

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